

ABSTRACT OF THE DISCLOSURE

There is described a semiconductor device having a storage
node capacitor structure suitable for rendering memory cells
5 compact, and storage nodes are prevented from tilting. The
device includes a storage node which has a vertical surface
extending in the direction perpendicular to the surface of a
semiconductor substrate, and a dielectric film for tilt
prevention purposes which is brought into close contact with the
10 side surface of the vertical surface and which prevents the
vertical surface from tilting.